

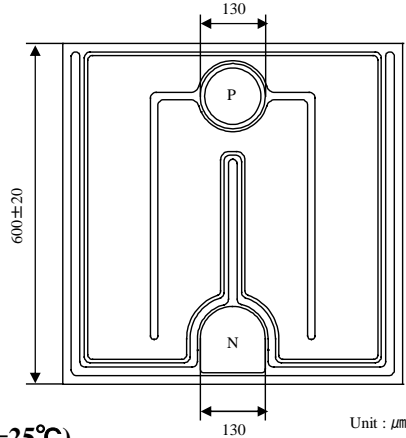
# ULTRA VIOLET LED Chip

NS365C-3SAA  
NS375C-3SAA

## (1) Chip Description

### ● Mechanical Specification

Description	Dimension
Emission Area	512 $\mu\text{m}$ x 535 $\mu\text{m}$
Bottom Area	600 $\mu\text{m}$ x 600 $\mu\text{m}$ $\pm$ 20 $\mu\text{m}$
Chip Thickness	120 $\mu\text{m}$ $\pm$ 10 $\mu\text{m}$
N Bonding Pad Electrode	125 $\mu\text{m}$ $\pm$ 5 $\mu\text{m}$
P Bonding Pad Electrode	125 $\mu\text{m}$ $\pm$ 5 $\mu\text{m}$



### ● Material

Substrate : Sapphire

Epitaxial Layer : GaN Based Material

N Bonding Pad Electrode : Au alloy

P Bonding Pad Electrode : Au alloy

## (2) Optical and Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	NS365C-3SAA	$V_F$ $I_F=100\text{mA}$	3.2	3.6	4.2	V
	NS375C-3SAA		3.2	3.9	4.2	
Reverse Current	$I_R$	$V_R=5\text{V}$	-	-	10	$\mu\text{A}$
Peak Wavelength*1	NS365C-3SAA	$\lambda_p$ $I_F=100\text{mA}$	363	-	370	nm
	NS375C-3SAA		375	-	380	
Full Width at Half Maximum	$\Delta\lambda$	$I_F=100\text{mA}$	10	-	20	nm
Optical Output Power *2	$P_o$	$I_F=100\text{mA}$	Refer to Rank Information			mW

\*1 Measurement error is  $\pm 2\text{nm}$

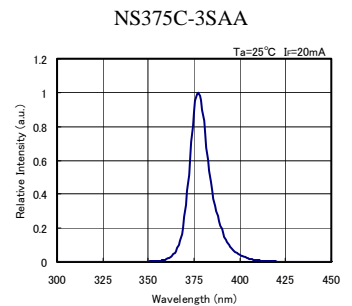
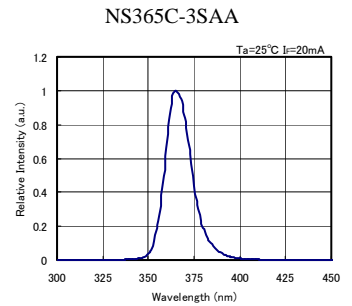
\*2 Measurement error is  $\pm 10\%$

### ■ Rank Information

Rank	Optical Output Power			NS365C-3SAA	NS375C-3SAA
	Min.	Typ.	Max.		
A1	5.0	-	10.0	○	
A2	10.0	-	15.0		
A3	15.0	-	20.0		
A4	20.0	-	25.0		ask*3
A5	25.0	-	30.0		○
A6	30.0	-	35.0		○

\*3 Please contact us for availability.

## (3) Spectrum



### CAUTION

- LEDs emit very strong UV radiation.
- Don't look directly into the LED light. UV radiation can harm your eyes.
- To prevent even inadequate exposure, wear protective eyewear.
- If LEDs are embedded in devices, please indicate warning labels against the UV light LED used.
- Keep out of reach of children.
- UV LED chips are very sensitive to static and surge. Take a full protection from static.

Specification and dimension are subject to change for improvement without notice.